



N 沟道增强型场效应晶体管

N-CHANNEL MOSFET

FHP100N2F10A/FHA100N2F10A

主要参数 MAIN CHARACTERISTICS

ID (Silicon Limited)	100 A
VDSS-min	200 V
Rdson-typ (@Vgs=10V)	9.6 mΩ
Qg-typ	64 nC

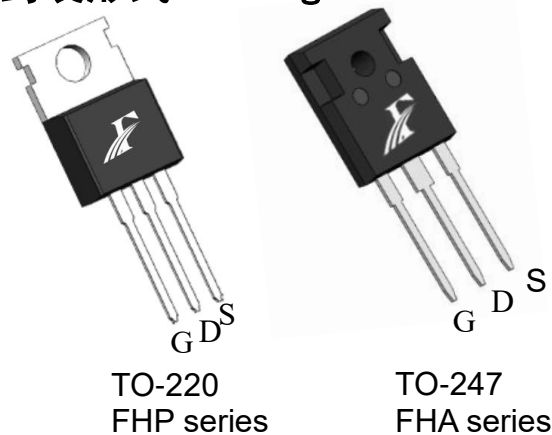
用途 APPLICATIONS

UPS	Uninterruptible Power Supplies
电机驱动	Motor Drive
逆变器	Power Management in Inverter System

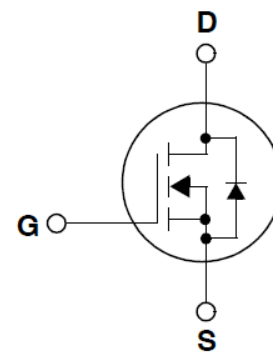
产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 12 pF)	Low Crss (typical 12 pF)
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
100%经过 Rg 测试	100% Rg tested
100%经过热阻测试	100% DVDS tested
RoHS 产品	RoHS product
SGT 工艺	SGT technology

封装形式 Package



等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项目 Parameter	符号 Symbol	数值 Value		单位 Unit
		FHP100N2F10A	FHA100N2F10A	
最高漏极—源极直流电压 Drain-Source Voltage	VDSS	200		V
连续漏极电流* Drain Current -continuous *	ID (Tc=25℃)	100		A
	ID (Tc=100℃)	72		A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	IDM	400		A
最高栅源电压 Gate-Source Voltage	VGS	±20		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	EAS	364.5		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	IAR	27		A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	EAR	50		mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	5.0		V/ns
耗散功率 Power Dissipation	PD (TC=25℃)	173.6	329	W
	-Derate above 25℃	1.39	2.63	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	TJ, TSTG	150, -55~+150		℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	TL	300		℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature

电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏－源击穿电压 Drain-Source Voltage	BVDSS	Id=250μA, VGS=0V	200	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBVDSS/Δ Tj	Id=250μA, referenced to 25℃	-	0.2	-	V/℃
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	IDSS	VDS=200V,GS=0V, Tc=25℃	-	-	1	μA
		VDS=160V, Tc=125℃	-	-	100	μA
栅极体漏电流 Gate-body leakage current	IGSS (F/R)	VDS=0V, VGS =±20V	-	-	±100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	VGS(th)	VDS = VGS , ID=250μA	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	RDS(ON)	VGS =10V , ID=50A	-	9.6	10.5	mΩ
正向跨导 Forward Transconductance	gfs	VDS = 5V, ID=50A (note 4)	-	80	-	S
动态特性 Dynamic Characteristics						
栅电阻 Gate Resistance	Rg	f=1.0MHz,VDS OPEN	-	5.3	-	Ω
输入电容 Input capacitance	Ciss	VDS=100V, VGS =0V, f=1.0MHz	-	4870	-	pF
输出电容 Output capacitance	Coss		-	402	-	
反向传输电容 Reverse transfer capacitance	Crss		-	12	-	
开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	td(on)	VDS=100V, ID=50A, RG=1.6Ω VGS =10V (note 4, 5)	-	22	-	ns
上升时间 Turn-On rise time	tr		-	40	-	ns
延迟时间 Turn-Off delay time	td(off)		-	66	-	ns
下降时间 Turn-Off Fall time	tf		-	18	-	ns
栅极电荷总量 Total Gate Charge	Qg	VDS =100V , ID=50A , VGS =10V (note 4, 5)	-	64	-	nC
栅－源电荷 Gate-Source charge	Qgs		-	28	-	nC
栅－漏电荷 Gate-Drain charge	Qgd		-	7.9	-	nC
漏－源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	Is		-	-	100	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	ISM		-	-	400	A
正向压降 Drain-Source Diode Forward Voltage	VSD	VGS=0V, Is=50A	-	-	1.2	V
反向恢复时间 Reverse recovery time	trr	VGS=0V, Is=50A ,dIf/dt=100A/μs (note 4)	-	125	-	ns
反向恢复电荷 Reverse recovery charge	Qrr		-	0.6	-	μC

热特性 THERMAL CHARACTERISTIC

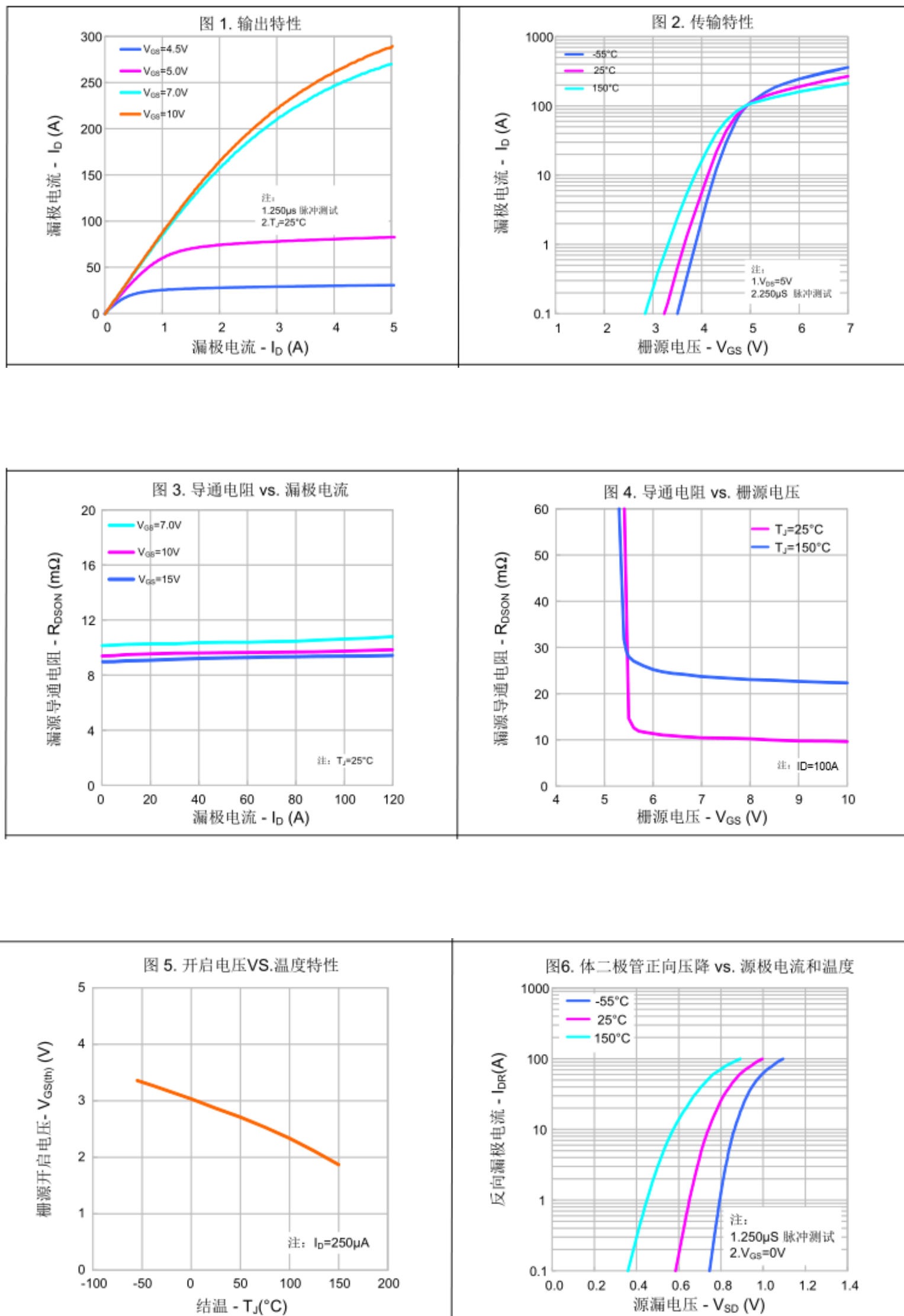
项目 Parameter	符号 Symbol	FHP100N2F10A	FHA100N2F10A	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	0.70	0.38	℃/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	62.5	40	℃/W

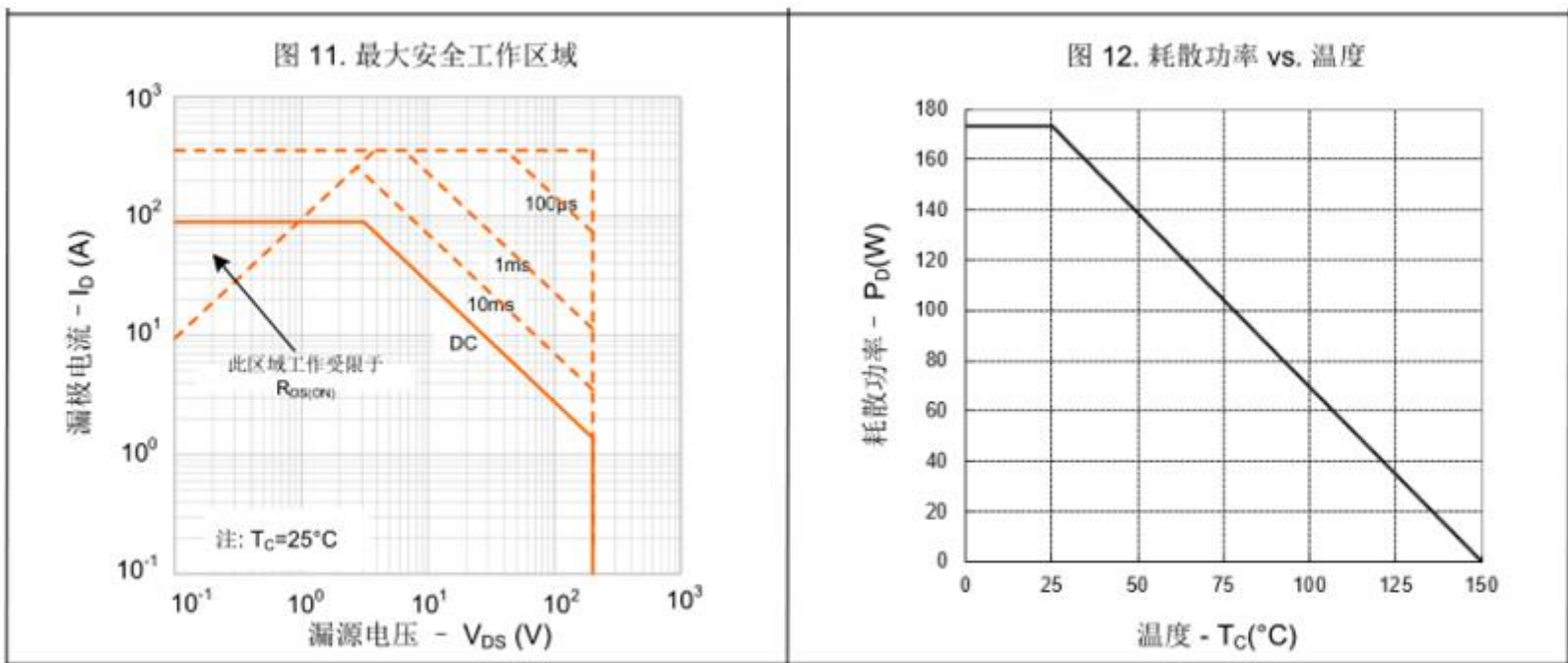
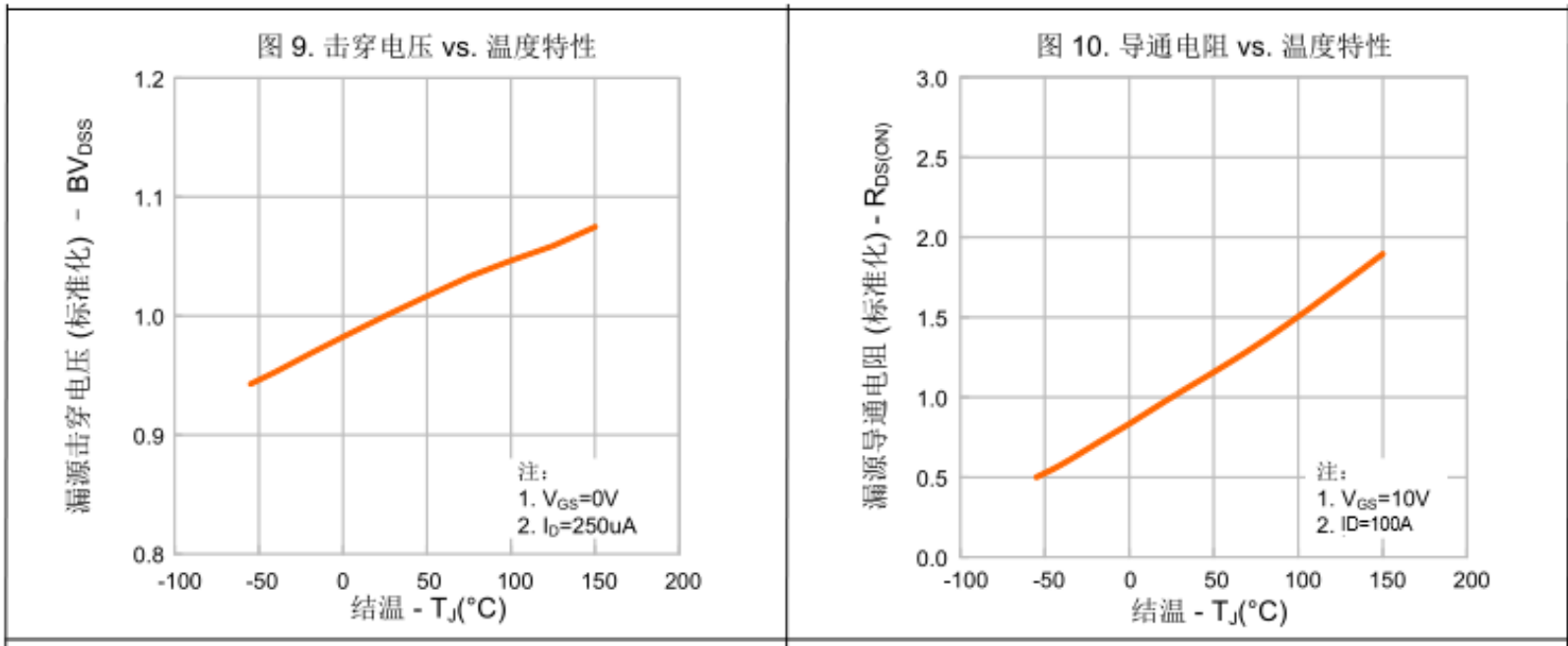
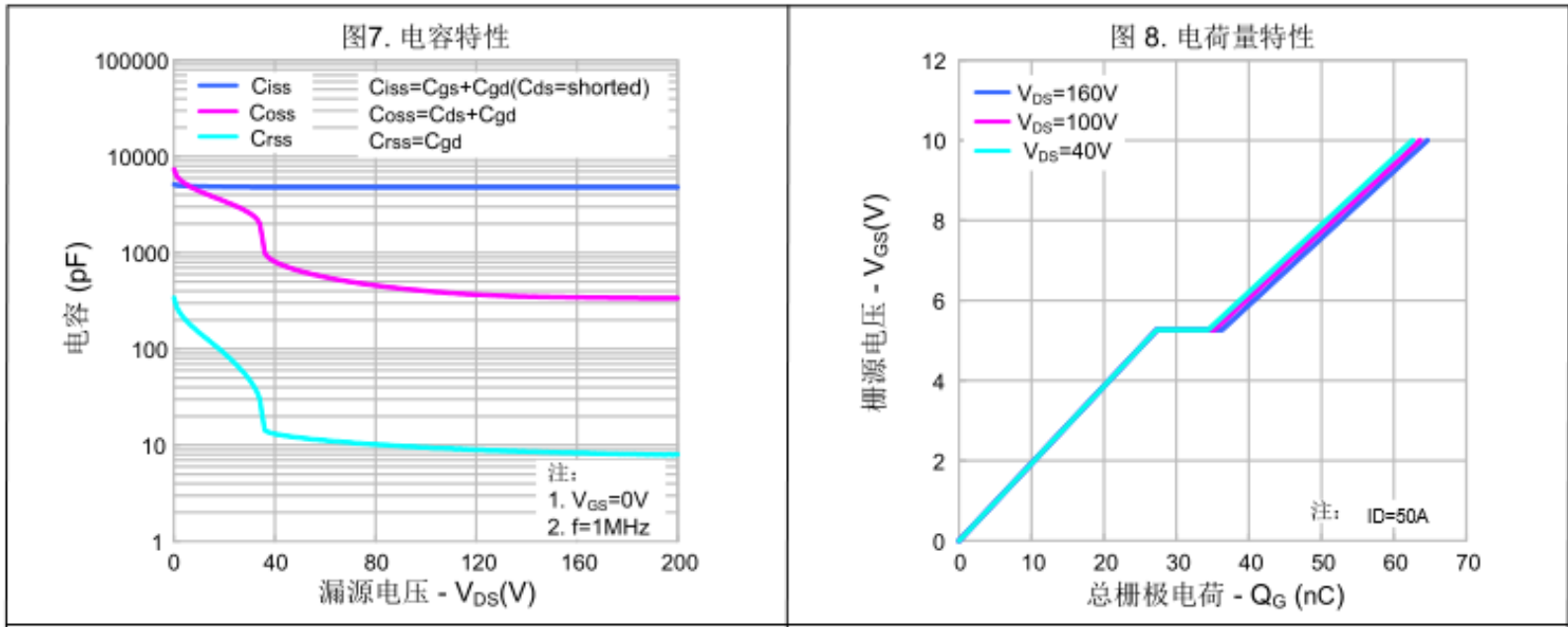
- 注释:
- 1: 脉冲宽度由最高结温限制
 - 2: L=1.0mH, VGS=10V, VDD=50V, RG=25 Ω,起始结温 TJ=25℃
 - 3: ISD ≤100A,di/dt ≤300A/μs,VDD≤BVDSS,起始结温 TJ=25℃
 - 4: 脉冲测试: 脉冲宽度 ≤300μs,占空比≤2%
 - 5: 基本与工作温度无关

- Notes:
- 1: Pulse width limited by maximum junction temperature
 - 2: L=1.0mH, VGS=10V, VDD=50V, RG=25 Ω,Starting TJ=25℃
 - 3: ISD ≤100A,di/dt ≤300A/μs,VDD≤BVDSS, Starting TJ=25℃
 - 4: Pulse Test: Pulse Width ≤300μs,Duty Cycle≤2%
 - 5: Essentially independent of operating temperature

Typical Characteristics

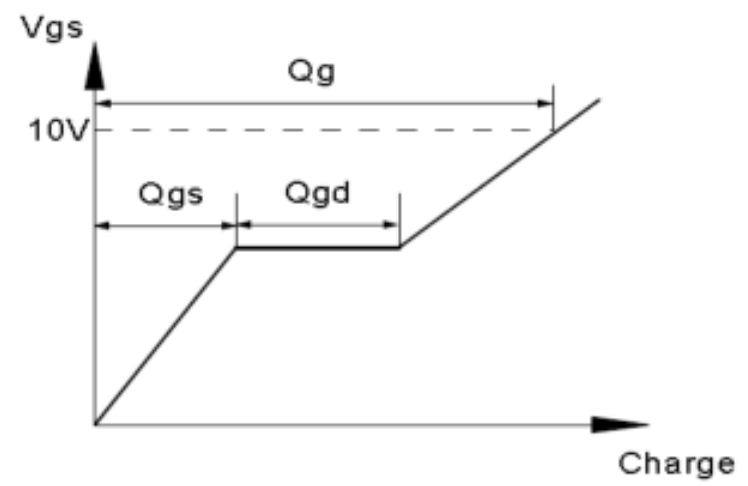
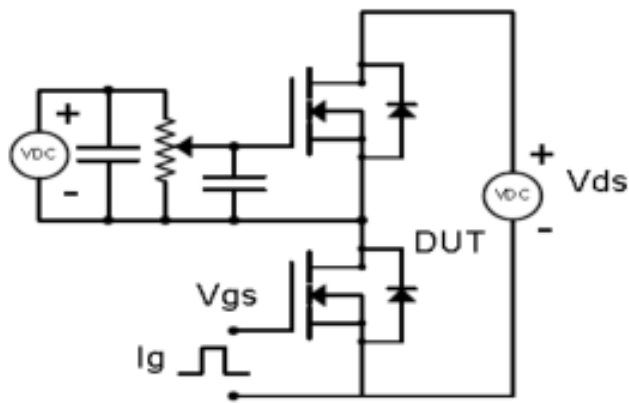
典型特性曲线



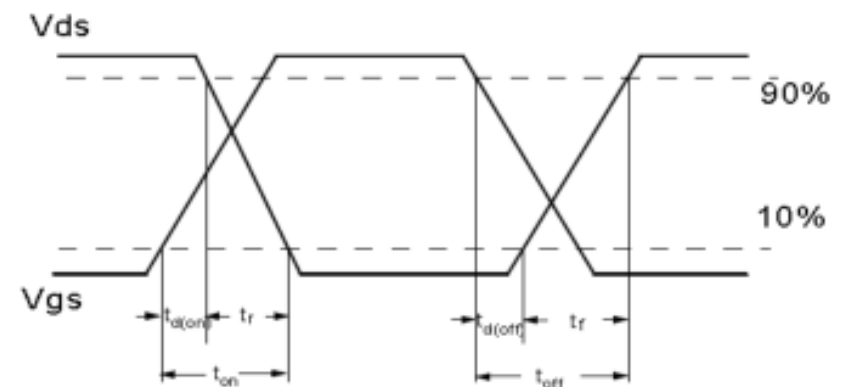
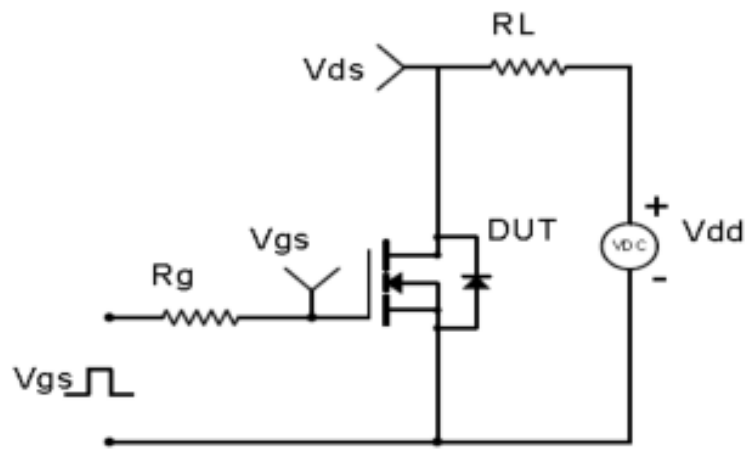


Test Circuit & Waveform

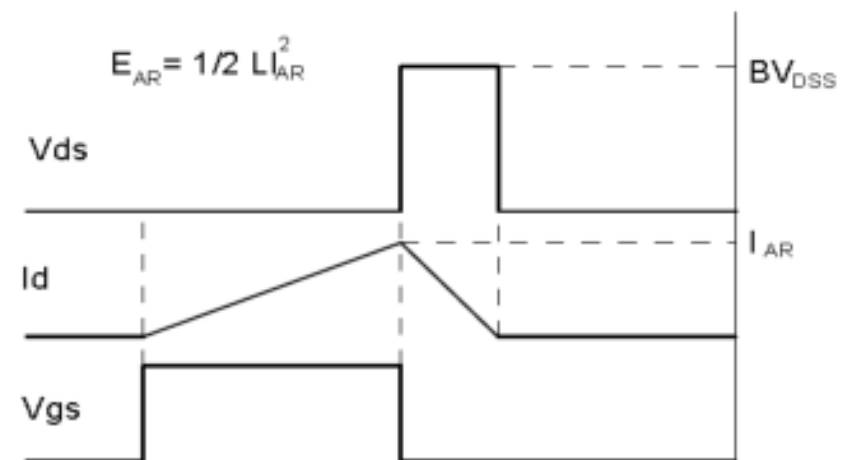
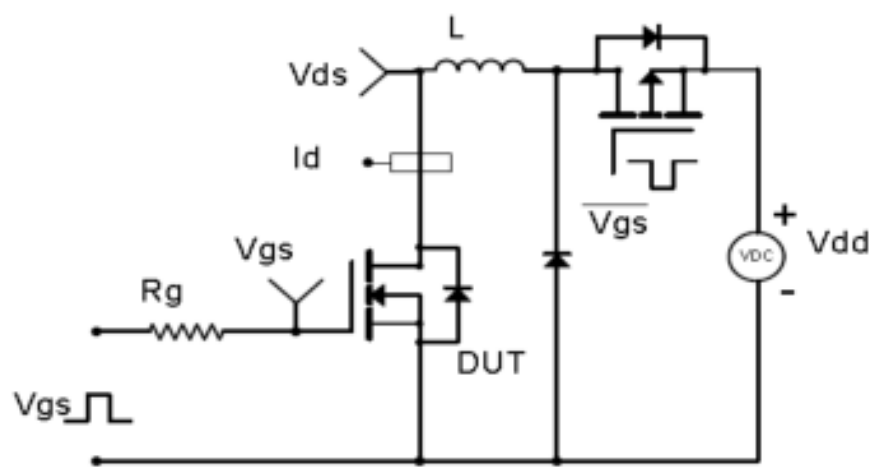
Gate Charge Test Circuit & Waveform



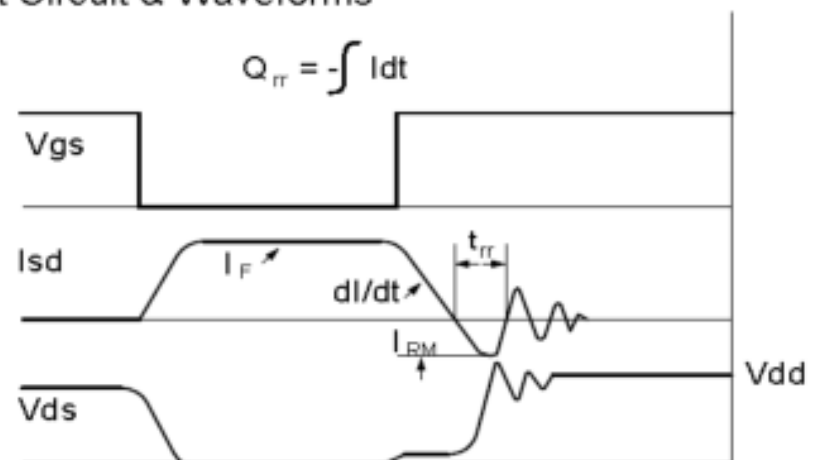
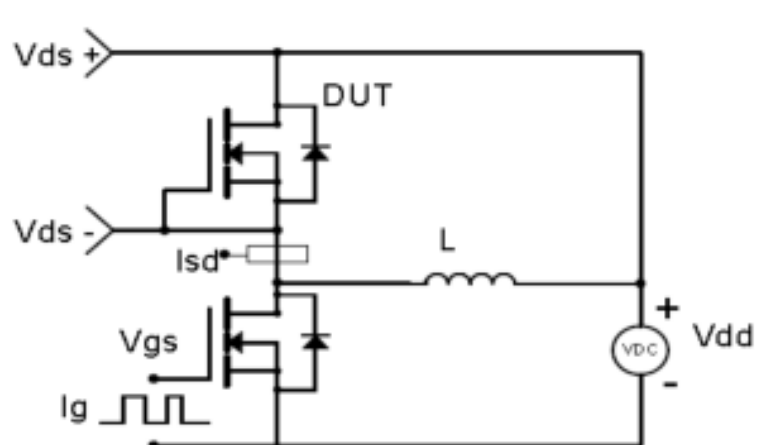
Resistive Switching Test Circuit & Waveforms



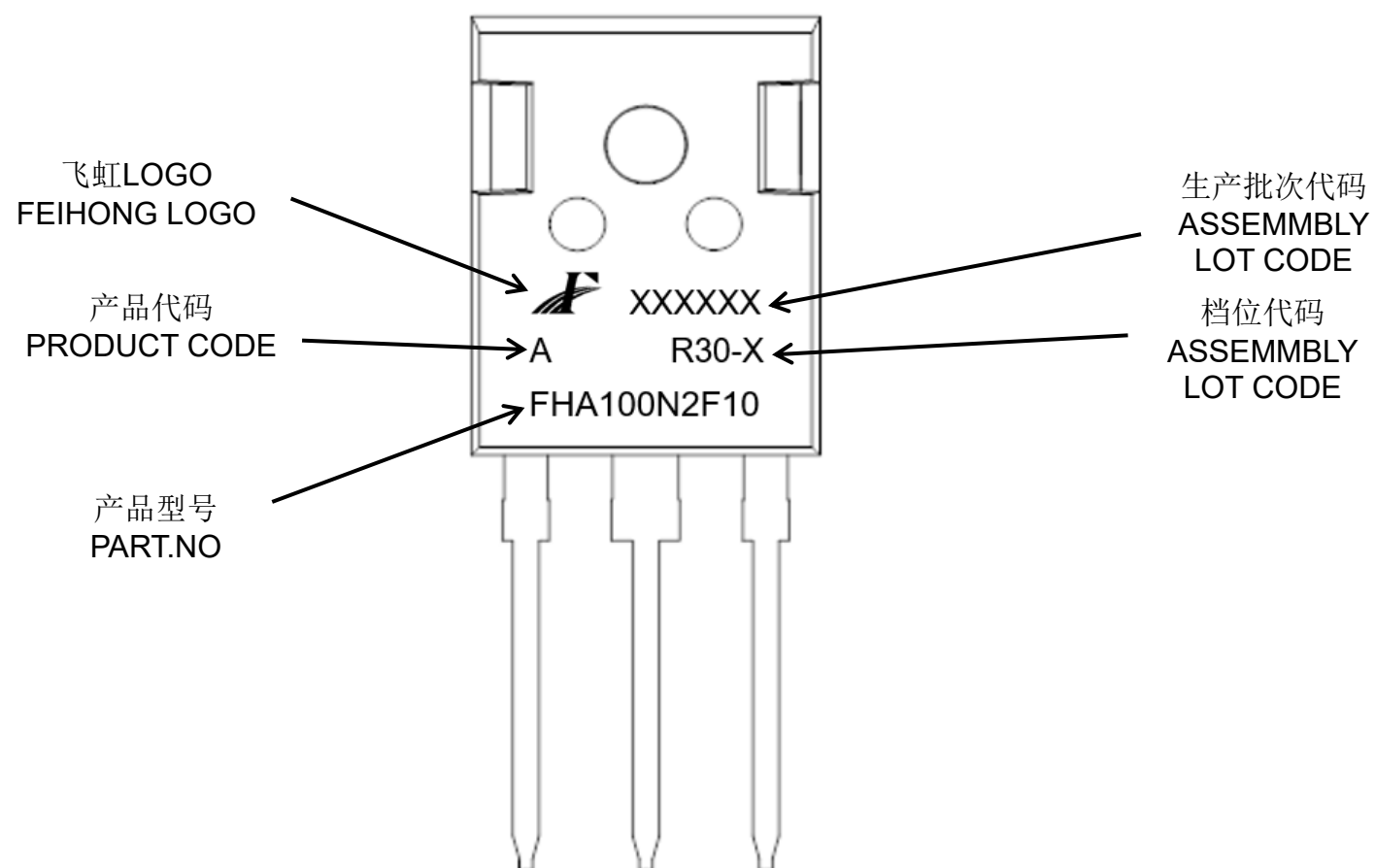
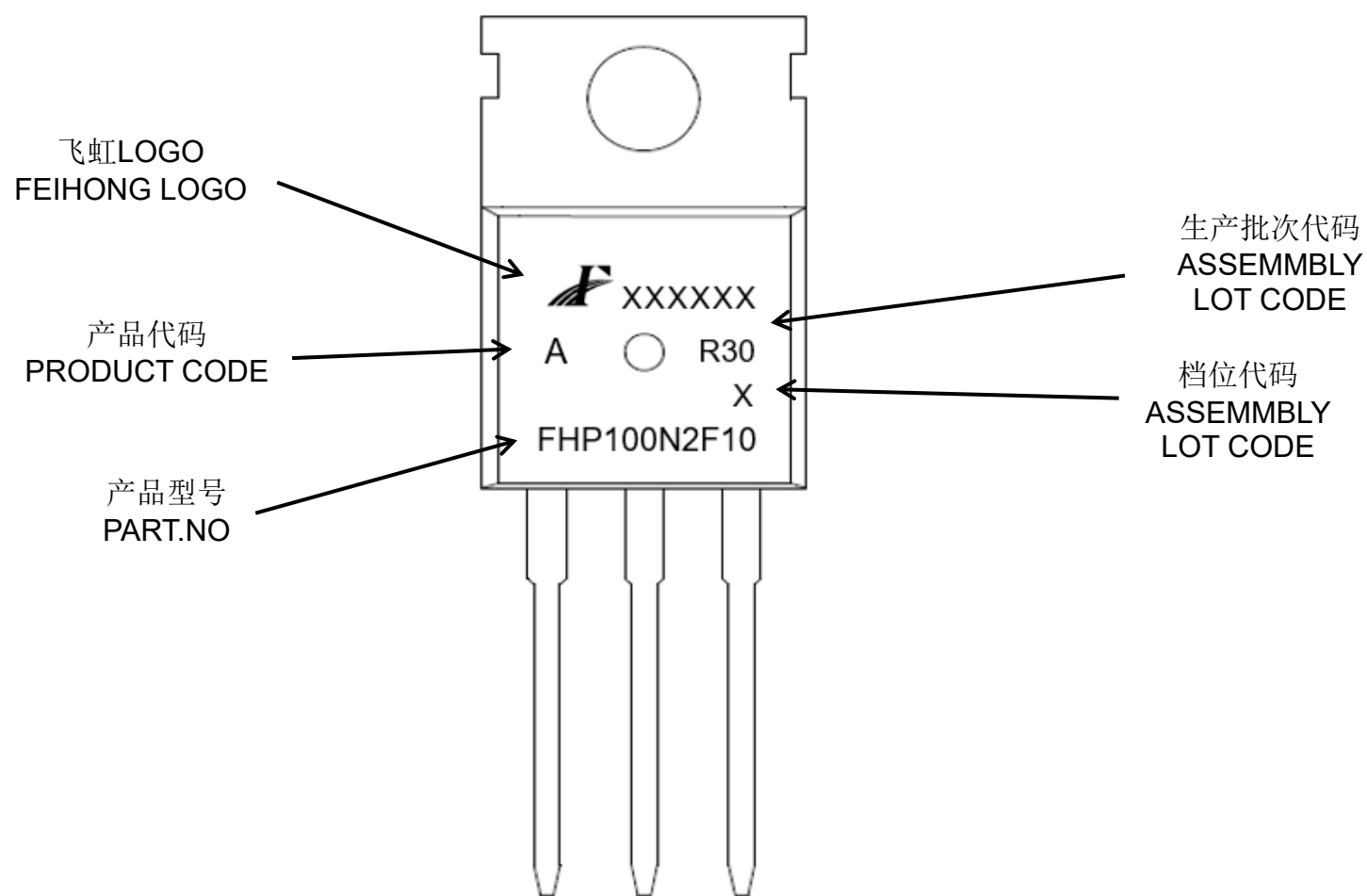
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



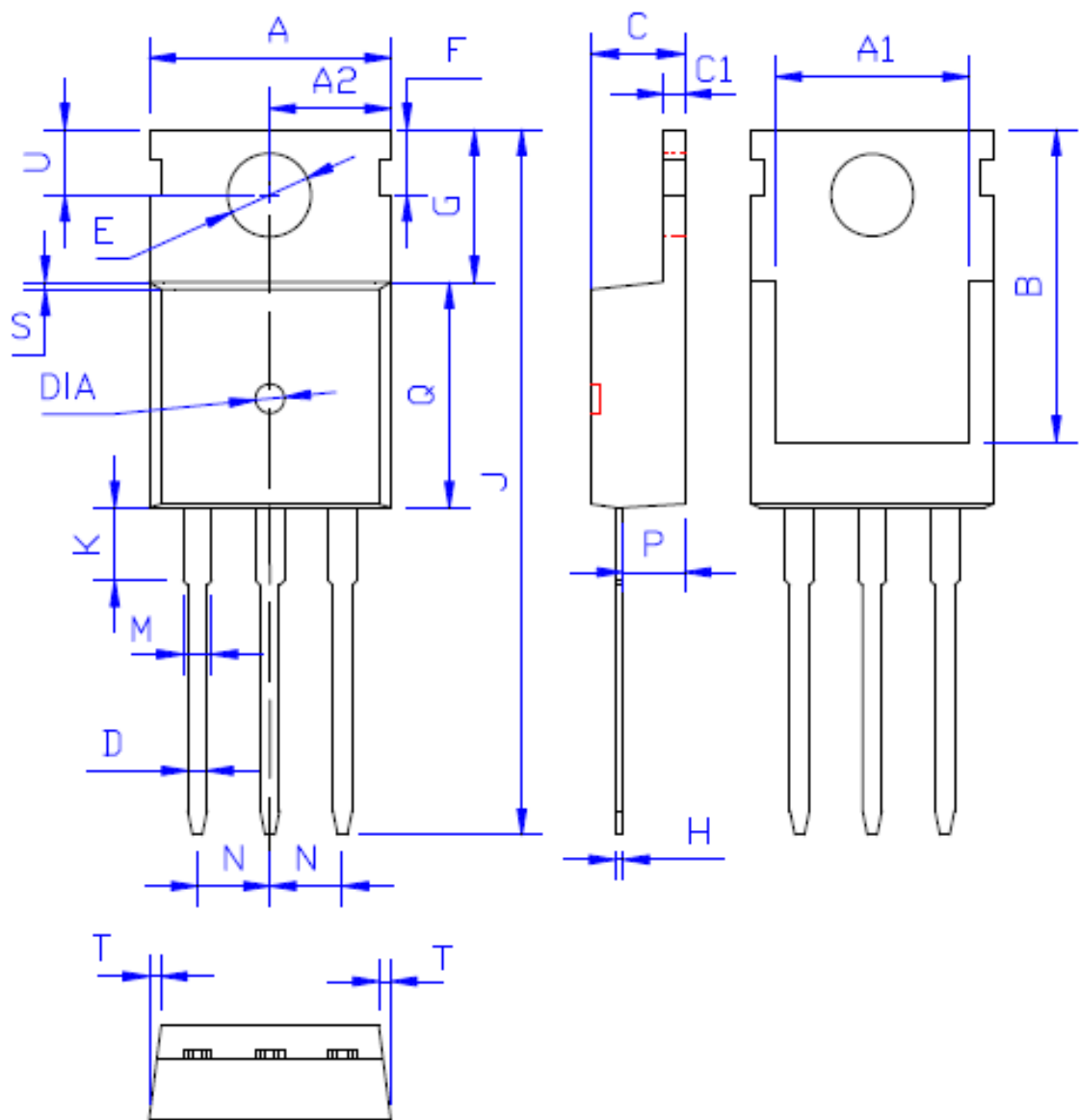
印记 Marking:



外形尺寸:

Package Dimension:

TO-220



DIM	MILLIMETERS
A	10.00±0.30
A1	8.00±0.30
A2	5.00±0.30
B	13.20±0.40
C	4.50±0.20
C1	1.30±0.20
D	0.80±0.20
E	3.60±0.20
F	3.00±0.30
G	6.60±0.40
H	0.50±0.20
J	28.88±0.50
K	3.00±0.30
M	1.30±0.30
N	Typical 2.54
P	2.40±0.40
Q	9.20±0.40
S	0.25±0.15
T	0.25±0.15
U	2.80±0.30
DIA	宽 1.50±0.10 深 0.50 MAX

(Unit: mm)

Package Dimension:

标注	尺寸(mm)
A	5.00 ± 0.05
A1	2.41 ± 0.05
b	1.2 ± 0.05
b1	3.05 ± 0.05
b2	2.05 ± 0.05
c	0.60 ± 0.05
c1	2.00 ± 0.05
D	15.80 ± 0.10
E1	3.60 ± 0.05
E2	3.70 ± 0.05
E3	7.19 ± 0.05
L	40.92 ± 0.10
L1	24.95 ± 0.10
L2	21.00 ± 0.10
L3	19.92 ± 0.10
L4	4.10 ± 0.05
e	5.44 ± 0.05
H	6.15 ± 0.05
h	2.50 ± 0.05
K	16.45 ± 0.10
M1	14.00 ± 0.10
M2	13.30 ± 0.10